# 2W 850 nm Multi-Mode VCSEL

#### **Product Overview**

SAIC's S-V850S20-000 is 850nm multi-mode top-emitter laser diode chip for use in IR illumination and sensing. The laser features include low threshold and operating currents, top-anode, bottom-cathode and non-hermetic design.

#### **Key Features**

- > 850nm multi-mode top-emitter
- Top-anode and Bottom-cathode configuration
- Low threshold and operating currents
- non-hermetic design



## **Applications**

- IR illumination
- sensing



#### **Electro-optical Characteristics**

Doromotoro	Symbol	Conditions	Specification/Rating			Unit	
Farameters	Symbol	Conditions	Min.	Тур.	Max.	Onit	
Threshold current	I <sub>th</sub>	T=25 °C		0.5		А	
Operating voltage	Vop	T=25 °C, I <sub>op</sub> =3.0A		2.0	2.2	V	
Series resistance	Rs	T=25 °C, I <sub>op</sub> =3.0A		0.2		Ω	
Slope efficiency	η	T=25 °C, I <sub>op</sub> =3.0A		0.95		W/A	
Output power	LOP	T=25 °C, I <sub>op</sub> =3.0A	1.9	2.2		W	
Beam divergence	<b>θ</b> <sub>D86</sub>	T=25 °C, Iop =3.0A		22		deg.	
Emission wavelength	λ	T=25 °C, I <sub>op</sub> =3.0A	840	850	860	nm	
Wavelength shift	dλ/dT	T=25 °C~85 °C		0.07		nm/ °C	
Conversion efficiency	PCE	T=25 °C		38		%	

Note: The testing condition is 0.3ms-pulse/1%-Duty.

## **Absolute Maximum Ratings**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Rating.	Unit
Reverse Voltage	Vr	5	V
Operating Temperature	T <sub>op</sub>	-20~85	٥C
Storage Temperature	T <sub>st</sub>	-40~100	٥C
Mounting Temperature (max. 10 sec)	Tm	260	°C



#### **LIV Characteristics**

Typical Performance Curves at 25  $^\circ\!\mathrm{C}\,$  .



# **VCSEL Chip Dimensions**

Parameter	Symbol	Min.	Тур.	Max.	Unit
Die Length	L	960	980	1000	um
Die Width	W	960	980	1000	um
Die Thickness	Т	85	100	115	um
Bonding pad diameter	D <sub>pad</sub>	104	107	110	um
Emitter count	#.E		452		ea





Datasheet

#### **RoHS Compliance**

Xiamen Sanan Integrated Circuit is fully committed to environment protection and sustainable development and has set in place a comprehensive program for removing polluting and hazardous substances from all of its products. The relevant evidence of RoHS compliance is held as part of our controlled documentation for each of our compliant products. RoHS compliance parts are available to order, please refer to the ordering information section for further details.

#### **Ordering Information**

Product Code	form	package
S-V850S20-000	2W	850 nm Multi-Mode VCSEL Chip

#### **Important Notice**

Performance data, figures, tables, charts, and any illustrative material provided in this data sheet are typical and must be specifically confirmed in writing with Sanan before they become applicable to any particular order or contract. In accordance with the Sanan policy of continuous improvement specifications may change without notice. Further details are available from Sanan customer contact.